

N-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
8	0.047 at V _{GS} = 4.5 V	4.0 ^a	4.24 nC
	0.051 at V _{GS} = 2.5 V	4.0 ^a	
	0.058 at V _{GS} = 1.8 V	4.0 ^a	
	0.069 at V _{GS} = 1.5 V	4.0 ^a	

FEATURES

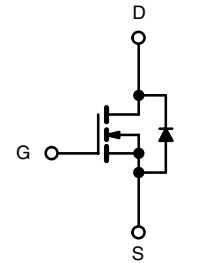
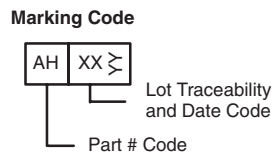
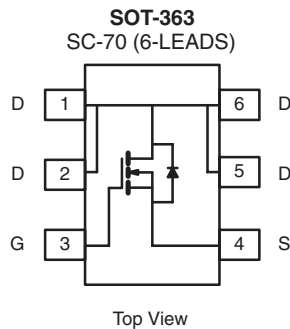
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 1.5 V Rated
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switch for Portable Applications
 - Guaranteed Operation at V_{GS} = 1.5 V
 - Critical for Optimized Design and Space Savings



Ordering Information: Si1450DH-T1-E3 (Lead (Pb)-free)
Si1450DH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	8	V	
Gate-Source Voltage	V _{GS}	± 5		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	6.04 ^a	
		T _C = 70 °C	4.8 ^a	
		T _A = 25 °C	4.53 ^a	
		T _A = 70 °C	3.62 ^a	
Pulsed Drain Current	I _{DM}	15	A	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		
		T _A = 25 °C	1.3 ^c	
Maximum Power Dissipation	P _D	T _C = 25 °C	2.78	
		T _C = 70 °C	1.78	
		T _A = 25 °C	1.56 ^{b, c}	
		T _A = 70 °C	1.0 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	60	80	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	34	45		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 125 °C/W.

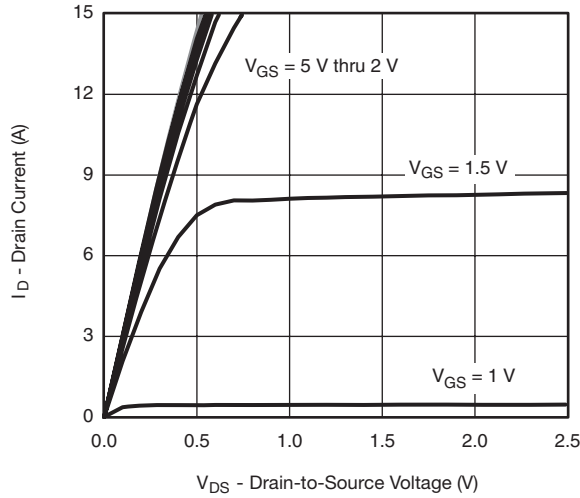
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		8.32		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-2.7		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.3		1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 100	ns
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 4.0\text{ A}$		0.039	0.047	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 4.0\text{ A}$		0.042	0.051	
		$V_{GS} = 1.8\text{ V}, I_D = 4.0\text{ A}$		0.048	0.058	
		$V_{GS} = 1.5\text{ V}, I_D = 1.28\text{ A}$		0.053	0.069	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 4\text{ V}, I_D = 4.0\text{ A}$		15.5		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		535		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			61		
Total Gate Charge	Q_g	$V_{DS} = 4\text{ V}, V_{GS} = 5\text{ V}, I_D = 4.0\text{ A}$		4.7	7.05	nC
		$V_{DS} = 4\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4.0\text{ A}$		4.24	6.4	
Q_{gs}			1.2			
Q_{gd}			0.810			
Gate Resistance	R_g	$f = 1\text{ MHz}$		7.3	11	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 4\text{ V}, R_L = 1.11\text{ }\Omega$ $I_D \cong 3.6\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		8	12	ns
Rise Time	t_r			73	110	
Turn-Off Delay Time	$t_{d(off)}$			18	27	
Fall Time	t_f			5	7.5	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			2.6	A
Pulse Diode Forward Current	I_{SM}				15	
Body Diode Voltage	V_{SD}	$I_S = 2.6\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2.6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		14.3	21.45	ns
Body Diode Reverse Recovery Charge	Q_{rr}			3.6	5.4	nC
Reverse Recovery Fall Time	t_a			6.8		ns
Reverse Recovery Rise Time	t_b			7.5		

Notes:

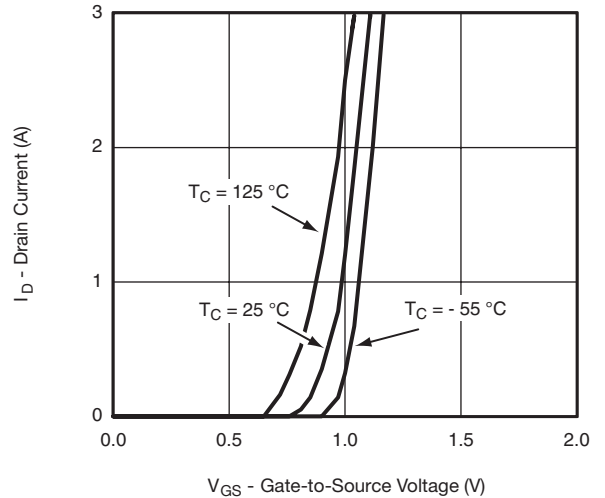
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

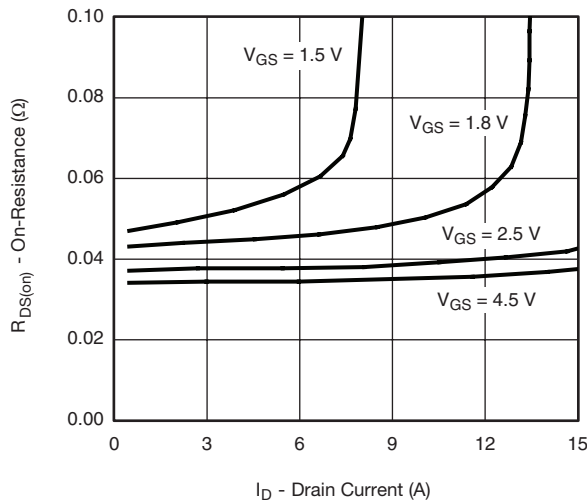
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



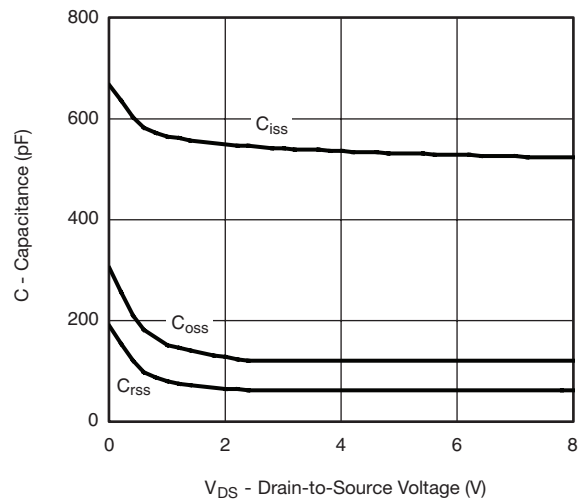
Output Characteristics



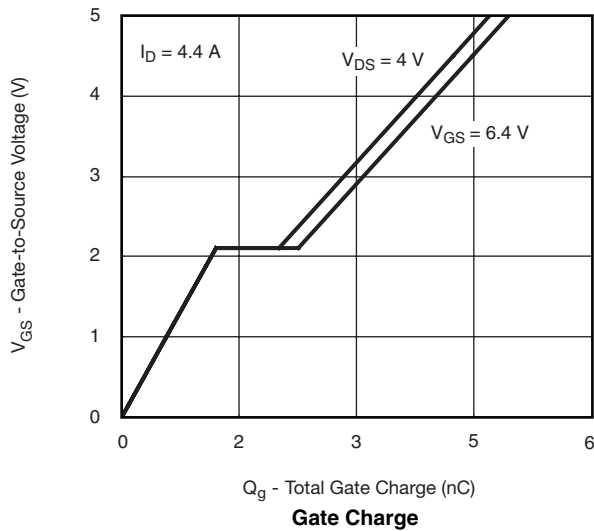
Transfer Characteristics



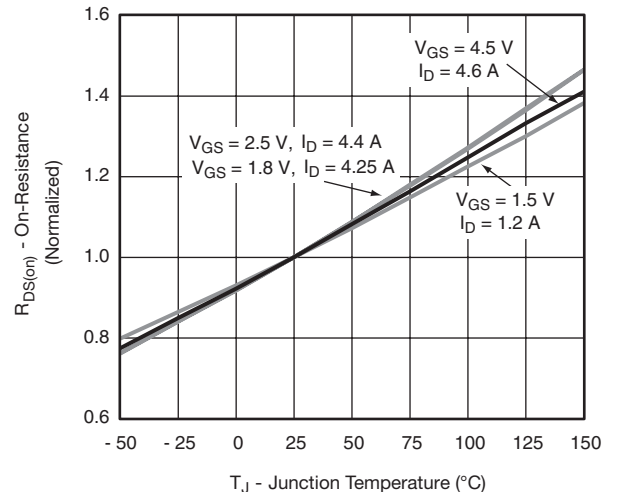
$R_{DS(on)}$ vs. Drain Current



Capacitance

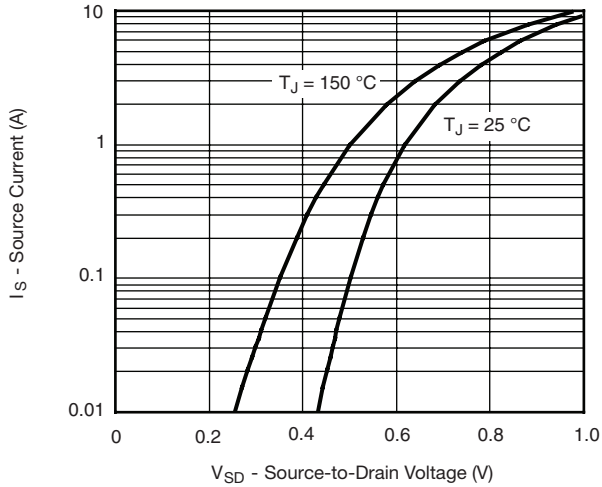


Gate Charge

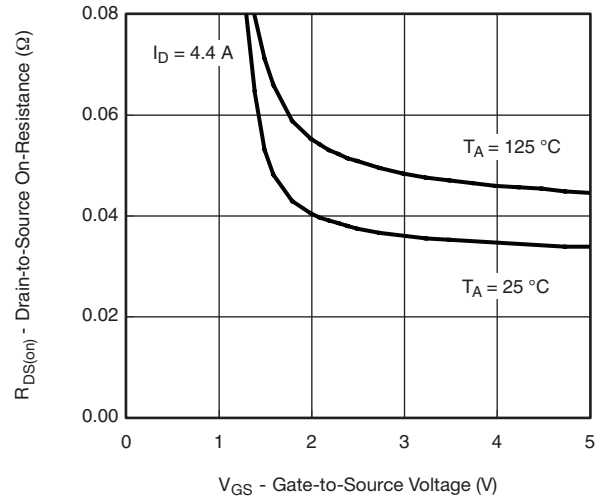


On-Resistance vs. Junction Temperature

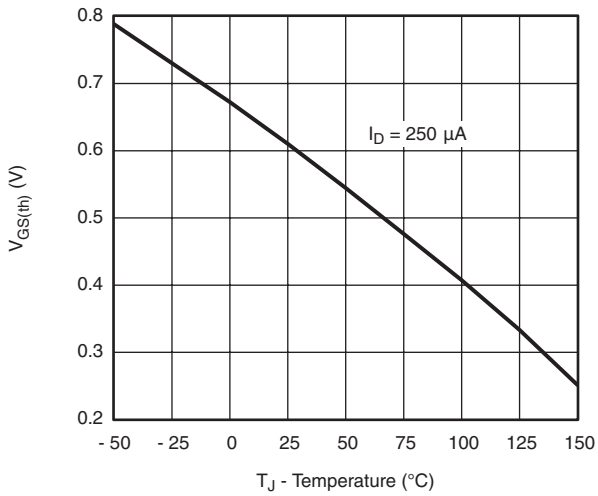
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



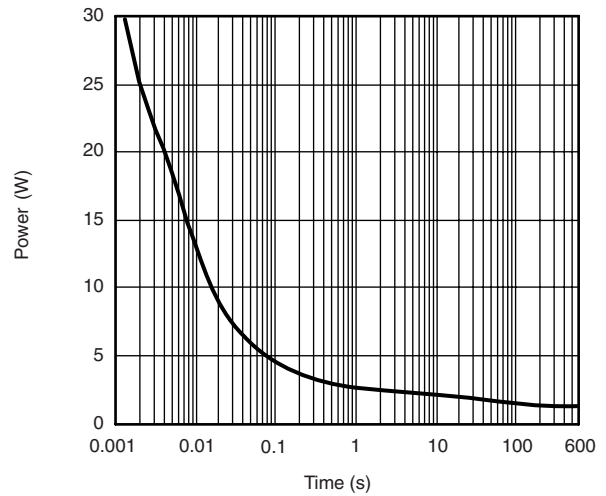
Forward Diode Voltage vs. Temperature



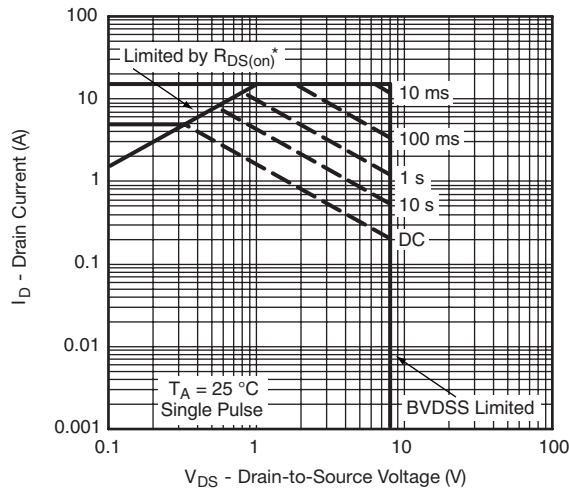
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage



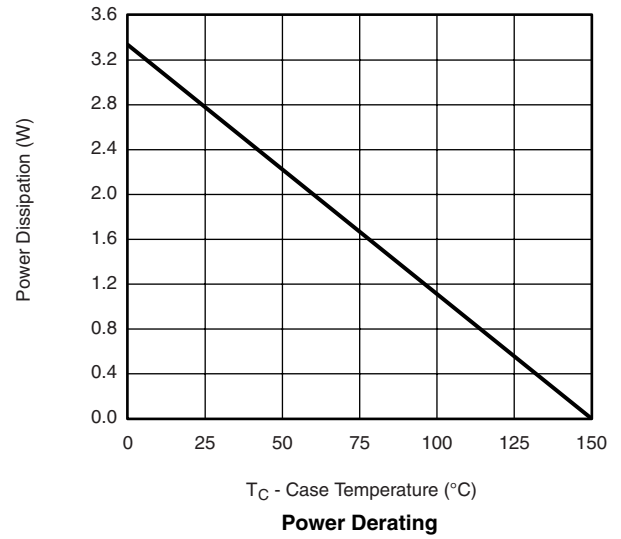
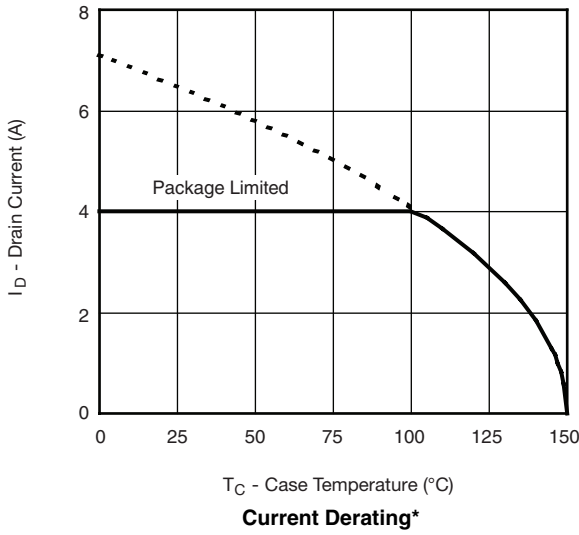
Single Pulse Power



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

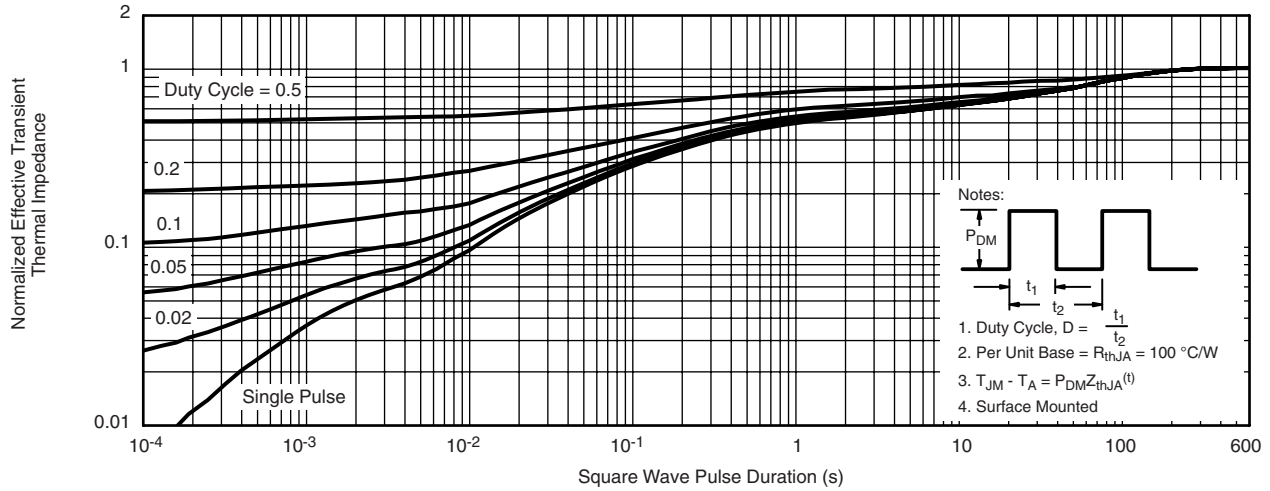
Safe Operating Area, Junction-to-Case

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

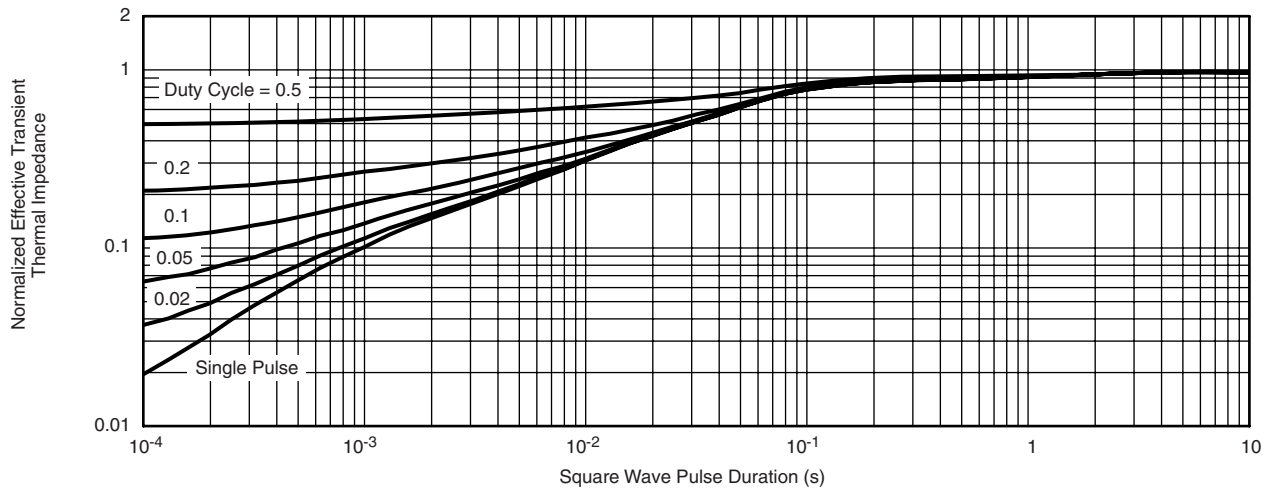


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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